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Contents

Editorial	219
KROK F., KOŁODZIEJ J.J., SUCH B., PIATKOWSKI P., SZYMONSKI M., ODENDAAL R.Q., MALHERBE B., Low energy ion beam-induced modification of InSb surface studied at nanometric scale	221
MICZEK M., ADAMOWICZ B., HASEGAWA H., Characterization of electronic properties of InP(100) surfaces from computer-aided analysis of photoluminescence	227
GLĄDYSZEWSKI L., Ultra-low frequency spectra for Li ⁺ ion thermoemission noise	235
JAKUBCZYK E., JAKUBCZYK M., Changes of properties during the annealing Fe ₂₈ Co ₅₀ Si ₉ B ₁₃ and Fe ₂₈ Ni ₅₀ Si ₉ B ₁₃ metallic glasses	241
MAZUREK P., JAŁOCHOWSKI M., Ordering of the vicinal Si(111) surface at low Au coverage	247
MITURA Z., Studies on the origin of reflection high energy electron diffraction oscillations observed during molecular beam epitaxy	253
OLESZKIEWICZ W., ROMISZOWSKI P., Growth of the optical layers in a stochastic simulation. Study of a film morphology	259
PIĄTKOWSKA A., JAGIELSKI J., TUROS A., ŚLUSARSKI L., BIELIŃSKI D., Influence of Ar and He implantation on surface morphology of polymers	267
TARGOSZ M., CZUBA P., SZYMONSKI M., Erythrocyte surface modification due to the pharmacological treatment studied with atomic force microscopy	275
TOMASZEWSKA A., STĘPIEŃ Z.M., H ₃ ⁺ -synthesis on the surface of d-transition metals during the process of field desorption	283
WASIAK M., BUGAJSKI M., MACHOWSKA-PODSIADŁO E., OCHALSKI T., KĄTCKI J., SARZAŁA R.P., MAĆKOWIAK P., CZYSZANOWSKI T., NAKWASKI W., CHEN J.X., OESTERLE U., FIORE A., ILEGEMS M., Optical gain saturation effects in InAs/GaAs self-assembled quantum dots	291
WIERTEL M., TARANKO E., TARANKO R., Influence of adsorbed atoms on the charge transfer in atom/ion – surface collision	301
SEK G., MISIEWICZ J., FORCHEL A., Photoreflectance spectroscopy of semiconductor device active regions: quantum wells and quantum dots	307
BAK-MISIUK J., MISIUK A., DOMAGAŁA J., Defect structure changes in thin layers of semiconductors annealed under hydrostatic pressure	319
BRUDNIK A., CZAPŁA A., KUSIOR E., Optical properties of AlN thin films obtained by reactive magnetron sputtering	327
CHOCYK D., PRÓSZYŃSKI A., GLĄDYSZEWSKI G., LABAT S., GERGAUD P., THOMAS O., Determination of stress in Au/Ni multilayers by symmetric and asymmetric X-ray diffraction	333

GÓRECKA-DRZAZGA A., Plasma dry etching of monocrystalline silicon for the microsystem technology	339
GRUHN W., KITYK I.V., Optimized structure of $\text{SiC}_x\text{N}_y\text{-Si}(111)$ interfaces by molecular dynamics simulation	347
HRUBAN A., STRZELECKA S., WEGNER E., PAWLOWSKA M., GLADKI A., STEPNIEWSKI R., JASIŃSKI J., BOZEK R., Bonding with atomic rearrangement – new possibilities in material and devices technology	355
JAKIELA R., JASIK A., STRUPIŃSKI W., GÓRA K., KOSIEL K., WESOŁOWSKI M., Influence of the thermal annealing on hydrogen concentration in GaN layers – SIMS characterization	365
JALOCHOWSKI M., STRÓŻAK M., Optical anisotropy of Pb nanowires on Si(533) surface ...	373
KUDRAWIEC R., MISIEWICZ J., PASZKIEWICZ R., PASZKIEWICZ B., TŁACZAŁA M., Optical properties of nominally undoped n-type MOVPE GaN epilayers	381
MAZUREK P., DANILUK A., PAPROCKI K., Forming the high quality CoSi_2 by solid phase epitaxy	389
MISIUK A., BRYJA L., KATCKI J., RATAJCZAK J., Effect of uniform stress on SiO_2/Si interface in oxygen-implanted Si and SIMOX structures	397
OLESIK J., High-energy electron emission from MIS-structures	409
PIASECKI T., KOŚNIKOWSKI W., PASZKIEWICZ B., PANEK M., Computer controlling of MOVPE process	417
PIENKOS T., GLADYSZEWSKI L., CHOCYK D., PRÓSZYŃSKI A., GLADYSZEWSKI G., MARTIN F., JAOUEN C., Measurements of stress during ion irradiation	421
SŁÓWKO W., DRZAZGA W., Non-standard techniques of surface characterization in scanning electron microscope	425
WÓJCIK A., PIWOŃSKI T., OCHALSKI T.J., KOWALCZYK E., BUGAJSKI M., GRZEGORCZYK A., MACHT L., HAFFOUZ S., LARSEN P.K., Photorefectance study of AlGaIn/GaN heterostructures grown by MOCVD process	431
BORATYŃSKI B., Transistors today – after 50 years in microelectronics	437
SARZAŁA R.P., Computer simulation of performance characteristics of (GaIn)(NAs) diode lasers	449
ZBROSZCZYK M., Numerical simulation of semiconductor lasers	461
BUGAJSKI M., ZBROSZCZYK M., SAJEWICZ P., MUSZAŁSKI J., High power AlGaAs/GaAs lasers with improved optical degradation level	469
CZYSZANOWSKI T., WASIAK M., MAĆKOWIAK P., SARZAŁA R.P., NAKWASKI W., Method of lines – the new vectorial approach to optical phenomena in diode lasers	477
KOŚNIKOWSKI W., PIASECKI T., Computer modelling of devices based on AlGaIn/GaN heterostructure	485
MAĆKOWIAK P., WASIAK M., CZYSZANOWSKI T., SARZAŁA R.P., NAKWASKI W., Designing guidelines for nitride VCSELS resonator	493
PASZKIEWICZ R., Application of selective area epitaxy for GaN devices	503
PRZESŁAWSKI T., WOLKENBERG A., REGIŃSKI K., KANIEWSKI J., Heterojunction $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}/\text{InP}$ magnetic field sensors fabricated by molecular beam epitaxy	511
SIOMA M., KANIEWSKI J., Numerical modelling of InGaAs infrared photovoltaic detectors	517
SZERLING A., WAWER D., HEJDUK K., PIWOŃSKI T., WÓJCIK A., MROZIEWICZ B., BUGAJSKI M., Reflectance study of $\text{SiO}_2/\text{Si}_3\text{N}_4$ dielectric Bragg reflectors	523
SZYMAŃSKI M., ZBROSZCZYK M., Numerical calculation of electron density distribution in modulation-doped GaAs/AlGaAs heterostructures	529

Editorial

We have noticed with a great pleasure that a significant growth of interest in the development of technological processes and characterisation methods of semiconductor structures, metal and dielectric thin-films has taken place in Poland. In the last few years, thanks to the financial support of KBN (State Committee for Scientific Research, Poland) and the funds received from the Fifth Frame European Programme, considerable progress occurred in the development of advanced quantum structures and devices in numerous research centres across the country.

In this issue, the theoretical and experimental results of the research conducted by many Polish laboratories are presented. Majority of the topics concerns surfaces and thin-film structures. Some works are devoted to the technology of III-V and other compound materials, including the latest results on the growth and characterisation of low-dimensional structures. Special attentions deserve papers presenting the newest and advanced measurements methods of surface examination and modification, especially on nano-metric scale.

Many papers report on the application of the results in the design and technology of advanced device structures. Computer aided modelling of physical phenomena or relevant device characteristics frequently supports the reported investigations.

The fact, that many authors of presented works is young research workers or Ph.D. students, should be noted with a great satisfaction. For the convenience of Readers this issue is divided into three parts: surface physics, thin film structures and contemporary semiconductor devices.

The Guest Editor would like to express his strong belief, that the presented material will contribute to further development of the research in the field of surface physics and modelling and characterisation of thin-film structures.

The articles presented in this issue were selected from the invited and contributed papers presented at the *Surface Physics and Thin-Film Structures Seminar* organised by the Polish Vacuum Society in Szklarska Poręba, Poland on May 13–17, 2002.

Dr. Marek Tłaczala
Guest Editor